

MPSW51, MPSW51A

One Watt High Current Transistors

PNP Silicon

Features

- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage MPSW51 MPSW51A	V_{CEO}	-30 -40	Vdc
Collector – Base Voltage MPSW51 MPSW51A	V_{CBO}	-40 -50	Vdc
Emitter – Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current – Continuous	I_C	-1000	mA dc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0 8.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	2.5 20	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

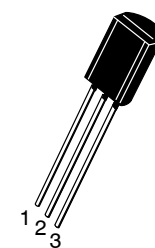
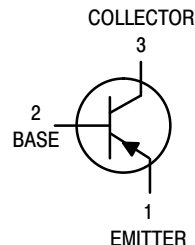
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

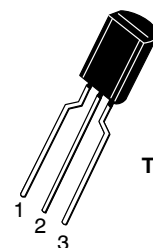


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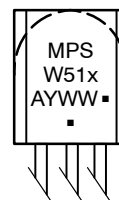
STRAIGHT LEAD



BENT LEAD

TO-92 1 WATT
(TO-226)
CASE 29-10
STYLE 1

MARKING DIAGRAM



x = 51A Devices
A = Assembly Location
Y = Year
WW = Work Week
■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MPSW51, MPSW51A

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 1) (I _C = –1.0 mAdc, I _B = 0)	V _{(BR)CEO}	–30 –40	– –	Vdc
Collector – Base Breakdown Voltage (I _C = –100 µAdc, I _E = 0)	V _{(BR)CBO}	–40 –50	– –	Vdc
Emitter – Base Breakdown Voltage (I _E = –100 µAdc, I _C = 0)	V _{(BR)EBO}	–5.0	–	Vdc
Collector Cutoff Current (V _{CB} = –30 Vdc, I _E = 0) (V _{CB} = –40 Vdc, I _E = 0)	I _{CBO}	– –	–0.1 –0.1	µAdc
Emitter Cutoff Current (V _{EB} = –3.0 Vdc, I _C = 0)	I _{EBO}	–	–0.1	µAdc

ON CHARACTERISTICS

DC Current Gain (I _C = –10 mAdc, V _{CE} = –1.0 Vdc) (I _C = –100 mAdc, V _{CE} = –1.0 Vdc) (I _C = –1000 mAdc, V _{CE} = –1.0 Vdc)	h _{FE}	55 60 50	– – –	–
Collector – Emitter Saturation Voltage (I _C = –1000 mAdc, I _B = –100 mAdc)	V _{CE(sat)}	–	–0.7	Vdc
Base – Emitter On Voltage (I _C = –1000 mAdc, V _{CE} = –1.0 Vdc)	V _{BE(on)}	–	–1.2	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (I _C = –50 mAdc, V _{CE} = –10 Vdc, f = 20 MHz)	f _T	50	–	MHz
Output Capacitance (V _{CB} = –10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	–	30	pF

1. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
MPSW51G	TO–92 (Pb–Free)	5000 Units / Bulk
MPSW51AG	TO–92 (Pb–Free)	5000 Units / Bulk
MPSW51RLRAG	TO–92 (Pb–Free)	2000 / Tape & Reel
MPSW51ARLRAG	TO–92 (Pb–Free)	2000 / Tape & Reel
MPSW51ARLRPG	TO–92 (Pb–Free)	2000 / Ammo Pack

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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TYPICAL CHARACTERISTICS

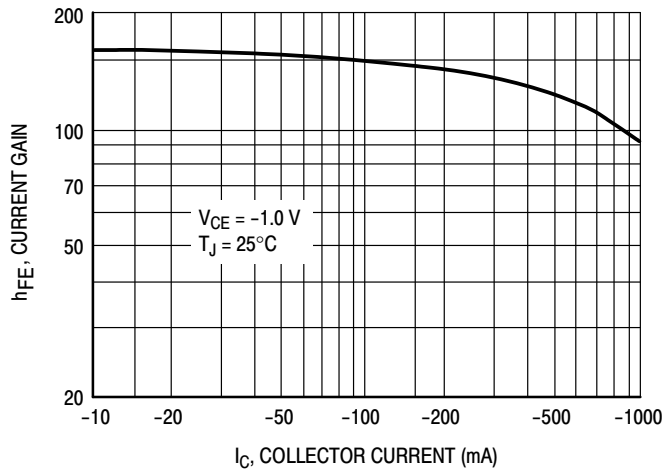


Figure 1. DC Current Gain

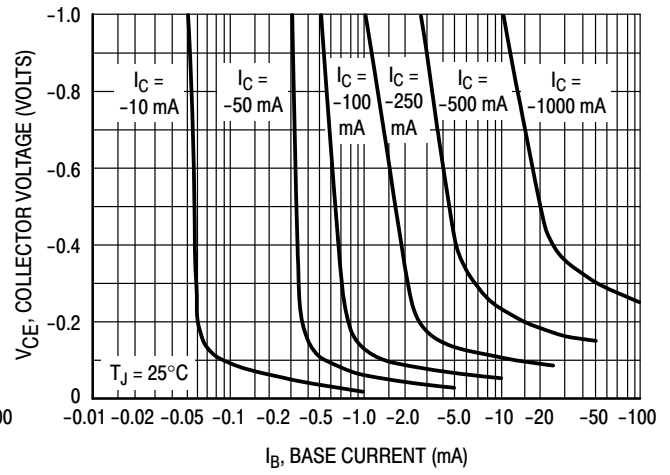


Figure 2. Collector Saturation Region

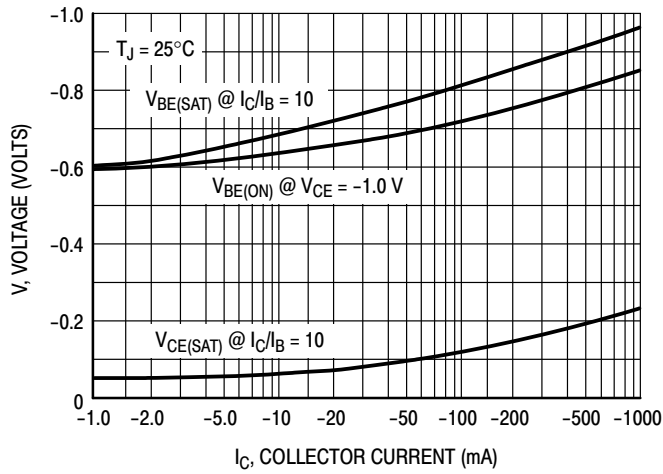


Figure 3. "ON" Voltages

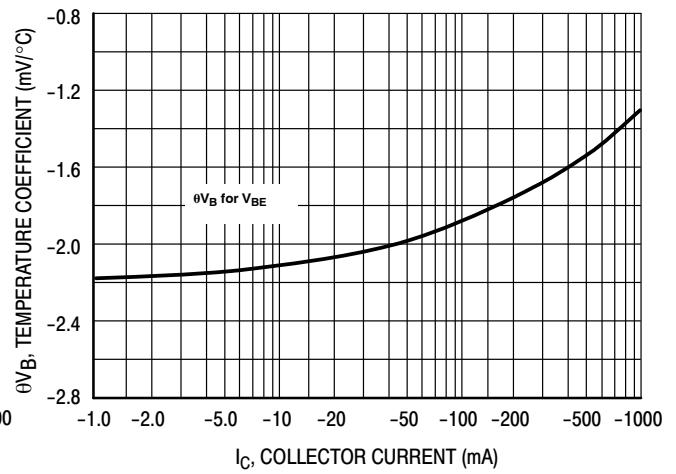


Figure 4. Temperature Coefficient

MPSW51, MPSW51A

TYPICAL CHARACTERISTICS

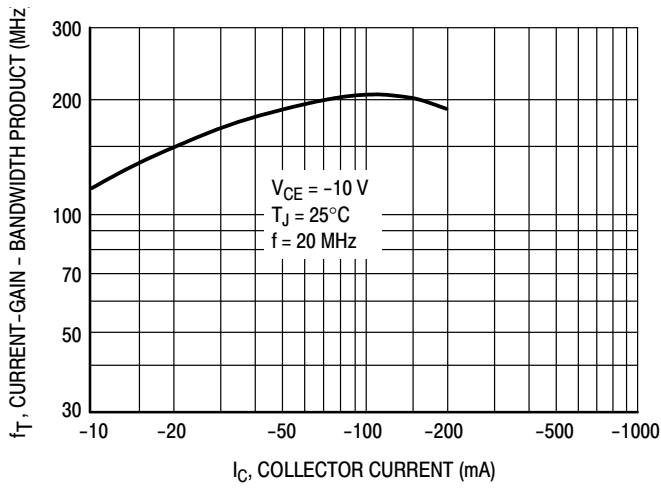


Figure 5. Current Gain — Bandwidth Product

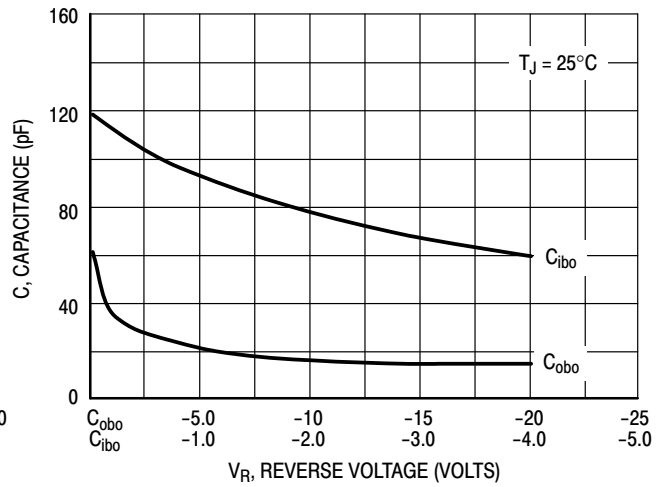


Figure 6. Capacitance

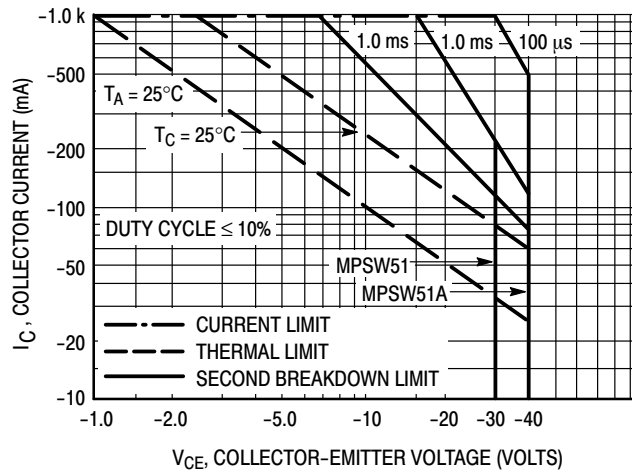


Figure 7. Active Region — Safe Operating Area

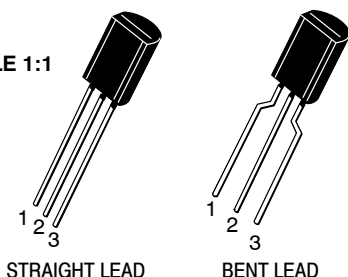
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1



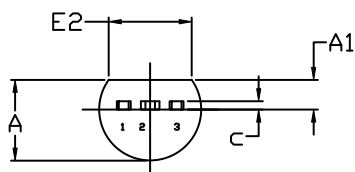
STRAIGHT LEAD

BENT LEAD

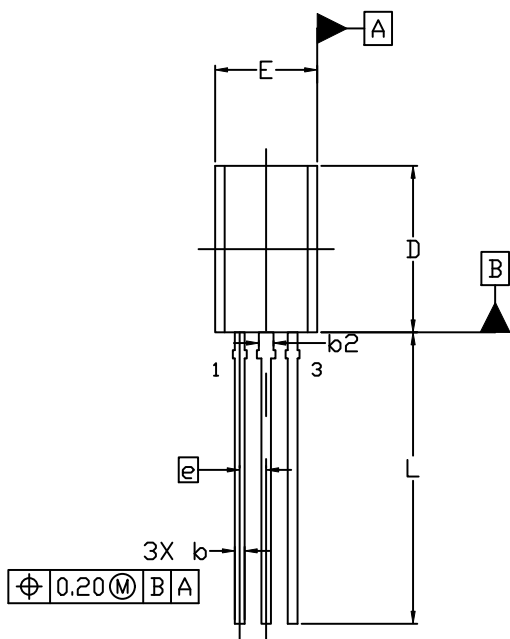
TO-92 (TO-226) 1 WATT
CASE 29-10
ISSUE D

DATE 05 MAR 2021

STRAIGHT LEAD



END VIEW



TOP VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
4. DIMENSION b AND b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION b2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	3.75	3.90	4.05
A1	1.28	1.43	1.58
b	0.38	0.465	0.55
b2	0.62	0.70	0.78
c	0.35	0.40	0.45
D	7.85	8.00	8.15
E	4.75	4.90	5.05
E2	3.90	---	---
e	1.27 BSC		
L	13.80	14.00	14.20

STYLES AND MARKING ON PAGE 3

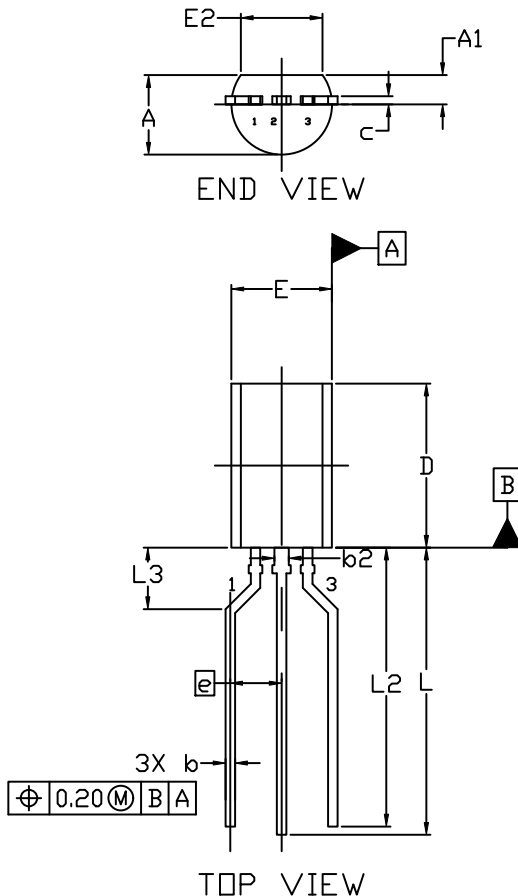
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ISSUE D

DATE 05 MAR 2021

FORMED LEAD



NOTES:

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D	7.85	8.00	8.15
E	4.75	4.90	5.05
E2	3.90	---	---
e	2.50 BSC		
L	13.80	14.00	14.20
L2	13.20	13.60	14.00
L3	3.00 REF		

STYLES AND MARKING ON PAGE 3

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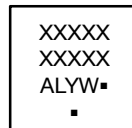
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DATE 05 MAR 2021

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 2: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. DRAIN 2. SOURCE 3. GATE
STYLE 6: PIN 1. GATE 2. SOURCE & SUBSTRATE 3. DRAIN	STYLE 7: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 8: PIN 1. DRAIN 2. GATE 3. SOURCE & SUBSTRATE	STYLE 9: PIN 1. BASE 1 2. EMITTER 3. BASE 2	STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 11: PIN 1. ANODE 2. CATHODE & ANODE 3. CATHODE	STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2	STYLE 13: PIN 1. ANODE 1 2. GATE 3. CATHODE 2	STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE	STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2
STYLE 16: PIN 1. ANODE 2. GATE 3. CATHODE	STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER	STYLE 18: PIN 1. ANODE 2. CATHODE 3. NOT CONNECTED	STYLE 19: PIN 1. GATE 2. ANODE 3. CATHODE	STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE
STYLE 21: PIN 1. COLLECTOR 2. EMITTER 3. BASE	STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN	STYLE 23: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 24: PIN 1. EMITTER 2. COLLECTOR/ANODE 3. CATHODE	STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2
STYLE 26: PIN 1. V _{CC} 2. GROUND 2 3. OUTPUT	STYLE 27: PIN 1. MT 2. SUBSTRATE 3. MT	STYLE 28: PIN 1. CATHODE 2. ANODE 3. GATE	STYLE 29: PIN 1. NOT CONNECTED 2. ANODE 3. CATHODE	STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE
STYLE 31: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 32: PIN 1. BASE 2. COLLECTOR 3. EMITTER	STYLE 33: PIN 1. RETURN 2. INPUT 3. OUTPUT	STYLE 34: PIN 1. INPUT 2. GROUND 3. LOGIC	STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

**GENERIC
MARKING DIAGRAM***



XXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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